



#3A Andt.
M. Bruns
PATENT 9/3/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

HWANG et al.

Group Art Unit: 2814

Serial No.: 10/022,349

Examiner: D. Wille

Filed: December 20, 2001

For: A SINGLE-CHIP STRUCTURE OF SILICON GERMANIUM
PHOTODETECTOR AND HIGH-SPEED TRANSISTOR

RECEIVED
AUG 28 2002
TECHNOLOGY CENTER 2800

AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

This is in response to the Official Action of May 28, 2002, in connection with the above-identified application.

Please amend the above-identified application as follows.

IN THE CLAIMS:

Please cancel claims 1-19 without prejudice or disclaimer and add the following new claims to the application.

Sub B1 AT Gmt

20(New). A single-chip structure of silicon germanium photodetectors and high-speed transistors comprising:
a substrate;
a phototransistor, which is formed on a side of the substrate;
a high-speed bipolar transistor which is located on the opposite side of the phototransistor on substrate; and
a separated insulation-layer which separates the phototransistor and the high-speed bipolar transistor, consisting of the above components, a single-chip structure